TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ( $L^2$ - $\pi$ -MOSVI)

# **2SJ537**

# Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance : RDS (ON) = 0.16  $\Omega$  (typ.)

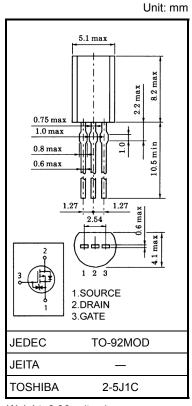
 $\bullet~$  High forward transfer admittance ~ :  $|\,Y_{fs}\,|\,$  = 3.5 S (typ.)

• Low leakage current :  $I_{DSS} = -100 \,\mu\text{A} \,(V_{DS} = -50 \,\text{V})$ 

• Enhancement-mode :  $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA)}$ 

#### Absolute Maximum Ratings (Ta = 25°C)

| Characteris               | stics                  | Symbol           | Rating  | Unit |  |
|---------------------------|------------------------|------------------|---------|------|--|
| Drain-source voltage      |                        | $V_{DSS}$        | -50     | V    |  |
| Drain-gate voltage (Ro    | <sub>GS</sub> = 20 kΩ) | $V_{DGR}$        | -50     | V    |  |
| Gate-source voltage       |                        | $V_{GSS}$        | ±20     | V    |  |
| Drain current             | DC (Note 1)            | I <sub>D</sub>   | -5      | Α    |  |
|                           | Pulse (Note 1)         | $I_{DP}$         | -15     | Α    |  |
| Drain power dissipation   | ı                      | $P_{D}$          | 0.9     | W    |  |
| Channel temperature       |                        | T <sub>ch</sub>  | 150     | °C   |  |
| Storage temperature range |                        | T <sub>stg</sub> | -55~150 | °C   |  |



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max | Unit |
|--|------------------------|-----|------|
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 138 | °C/W |

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.

Please handle with caution.

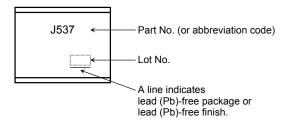
### **Electrical Characteristics (Ta = 25°C)**

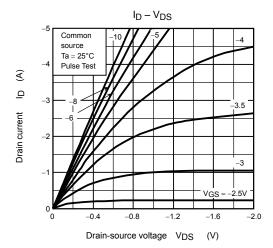
| Charac  | cteristics           | Symbol   | Test Condition  | Min  | Тур. | Max  | Unit |
|---|----------------------|--|---|------|------|------|------|
| Gate leakage cu                                 | ırrent               | I <sub>GSS</sub>                                 | V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V            | _    | _    | ±10  | μΑ   |
| Drain cut-off cu                                | rrent                | I <sub>DSS</sub>                                 | V <sub>DS</sub> = -50 V, V <sub>GS</sub> = 0 V            | _    | _    | -100 | μΑ   |
| Drain-source br<br>voltage                      | reakdown             | V (BR) DSS                                       | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V            | -50  | _    | _    | V    |
| Gate threshold v                                | /oltage              | V <sub>th</sub>                                  | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA           | -0.8 | _    | -2.0 | V    |
| Drain-source O                                  | N registance         | Pro (ON)   | $V_{GS} = -4 \text{ V}, I_D = -1.3 \text{ A}$             | _    | 0.27 | 0.34 |      |
| Drain-source ON resistance                      | R <sub>DS</sub> (ON) | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -2.5 A | _   | 0.16 | 0.19 | Ω    |      |
| Forward transfe                                 | r admittance         | Y <sub>fs</sub>                                  | $V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$            | 1.5  | 3.5  | -    | S    |
| Input capacitano                                | ce                   | C <sub>iss</sub>                                 |   | _    | 470  | _    |      |
| Reverse transfer capacitance                    |                      | C <sub>rss</sub>                                 | V <sub>DS</sub> = −10 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _    | 60   | _    | pF   |
| Output capacitance                              |                      | C <sub>oss</sub>                                 |   |      | 210  | _    |      |
| Switching time                                  | Rise time            | t <sub>r</sub>                                   | $V_{GS}_{-10V}$ $I_{D}=-2.5A$ $R_{L}=10\Omega$            | _    | 25   | _    |      |
|   | Turn-on time         | t <sub>on</sub>                                  |   | _    | 35   | _    | ns   |
|   | Fall time            | t <sub>f</sub>                                   |   | _    | 20   | _    |      |
|   | Turn-off time        | toff   | $V_{DD} = -25V$ Duty $\leq 1\%$ , $t_W = 10 \mu s$        | _    | 120  | -    |      |
| Total gate charge (Gate-source plus gate-drain) |                      | Qg   | V <sub>DD</sub> ≈ -40 V, V <sub>GS</sub> = -10 V,         | _    | 18   | _    |      |
| Gate-source charge                              |                      | Q <sub>gs</sub>                                  | $I_D = -5 \text{ A}$                                      |      | 13   | _    | nC   |
| Gate-drain ("miller") charge                    |                      | Q <sub>gd</sub>                                  |   | _    | 5    | _    |      |

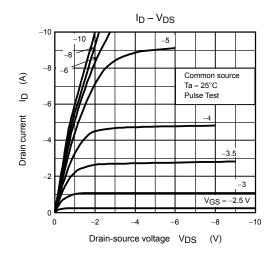
## Source-Drain Ratings and Characteristics (Ta = 25°C)

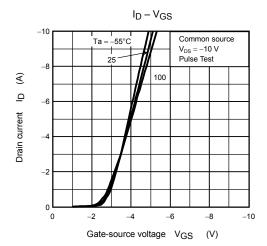
| Characteristics                           | Symbol           | Test Condition                  | Min | Тур. | Max | Unit |
|---|------------------|---------------------------------|-----|------|-----|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _                               | _   | _    | -5  | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _                               | _   | _    | -15 | Α    |
| Forward voltage (diode)                   | $V_{DSF}$        | $I_{DR}$ = -5 A, $V_{GS}$ = 0 V | 1   | _    | 1.5 | V    |

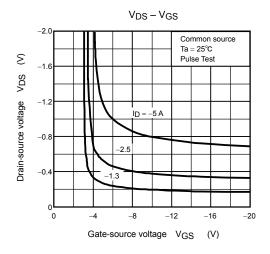
### Marking

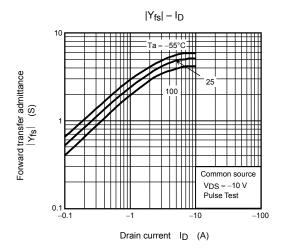


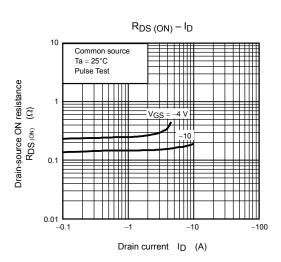




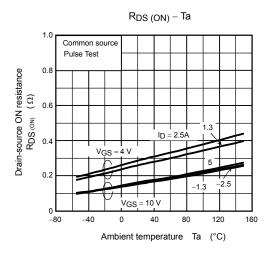


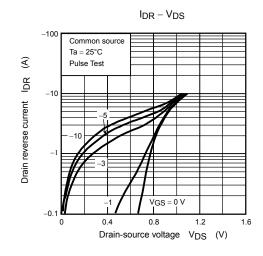


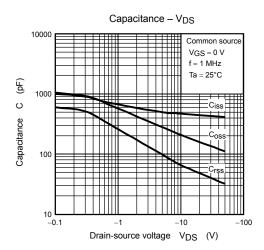


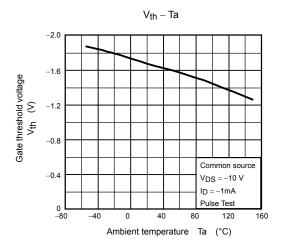


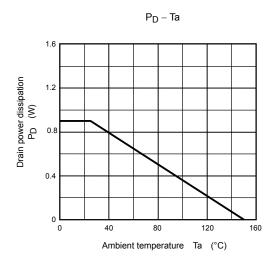
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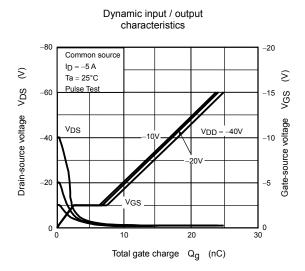


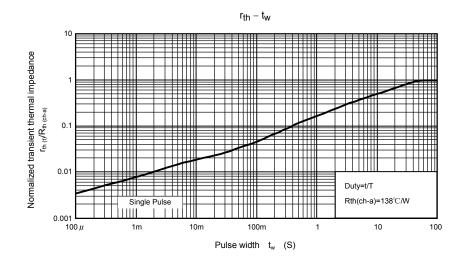


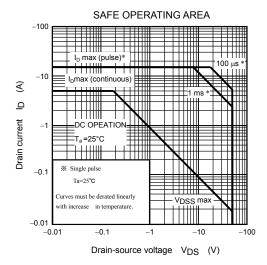












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